

## ABSTRACT OF THE DISCLOSURE

### **ETCHING SOLUTION HAVING SILICON OXIDE CORROSION INHIBITOR AND METHOD OF USING THE SAME**

Described herein is an etching solution suitable for the selective removal of polysilicon over silicon oxide from a microelectronic device, which comprises: water; at least one of a quaternary ammonium hydroxide compound; optionally at least one alkanolamine compound; a water-miscible solvent; at least one nitrogen containing compound selected from the group consisting of a C<sub>4-12</sub> alkylamine, a polyalkylenimine, a polyamine, a nitrogen-containing heterocyclic compound, a nitrogen-containing aromatic compound, or a nitrogen-containing heterocyclic and aromatic compound ; and optionally, a surfactant.

[No suitable figure]